

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(gate near electrode) with (source near electrode) with (top near surface\$1 near (die chip device)) with (back near surface\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/24 11:40
L2	4	(gate near electrode) same (source near electrode) same (top near surface\$1 near (die chip device)) same (back near surface\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/24 11:42
L3	0	(gate near electrode) same (source near electrode) same (top near surface\$1 near power near (die chip device))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/24 11:43
L4	19123	(gate near electrode\$1) with (source near electrode\$1) with (drain near electrode\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/24 13:47
L5	1458	4 and (power near (device\$1 die chip\$1 IC circuit\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/24 12:48
L6	50	(gate near electrode\$1) with (source near electrode\$1) with (drain near electrode\$1) with (power near (device\$1 die chip\$1 IC circuit\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/24 11:45
L7	0	(power near (device\$1 die chip\$1 IC circuit\$1)) with (built near in near diode\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/24 12:49
L8	0	(power near (device\$1 die chip\$1 IC circuit\$1)) and (built near in near diode\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/24 12:49

L9	6382	(power near (device\$1 die chip\$1 IC circuit\$1)) with diode\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/24 12:50
L10	81	9 and (schottky near barrier near diode\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/24 12:50
L11	32	(source near electrode\$1) with (drain near electrode\$1) with ((thermal heat) near (dissipat\$3 sink spreader))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/24 13:48